

## A New Generation Pixel Readout ASIC in 65nm CMOS for HL-LHC experiments

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## Introduction

Pixel detectors for HL-LHC experiments require the development of a new generation front-end chip to stand unprecedented radiation levels, very high hit rates and increased pixel granularity.

The main requirements for the HL-LHC detectors are:

- Small pixels:  $50x50 \ \mu m^2$
- Trigger up to 1 MHz with 12.8 µs latency
- For innermost layer:
  - $\circ$  Pixel hit rate up to 3 GHz/cm<sup>2</sup>
  - Radiation: 1 Grad in 10 years Ο
  - Data readout up to 4-5 Gbs/s





## CHIPIX65 demonstrator

- Main aspects:
- Small and complex 64x64 pixel matrix (50x50  $\mu$ m<sup>2</sup> each) featuring new solutions compatible with RD53A
- Two analog FEs (asynch and synch)  $\bullet$
- A novel digital architecture
- Bias network and monitoring
- Chip configuration based on SPI protocol
- Usage of CERN I/O library

## Design flow:

Digital-On-Top chip assembly Top-down hierarchical flow ullet

In this context the CHIPIX65 project has been approved by INFN in fall 2013, with the goals of:

- Developing a CHIP for PIXel detectors in 65nm CMOS technology for the first time in HEP experiments
- Propagate the use of the 65nm technology inside INFN •
- 8 sections involved (Bari, Lecce, Milano, Padova, Pavia/Bergamo, Perugia, Pisa, Torino)
- Funding member of the CERN RD53 collaboration



- Pixel matrix composed of 16x16 pixel regions (master and clone)
- A pixel region contains the digital architecture and the analog FEs



- Synchronous discriminator AC coupled to the first stage
- Offset compensation done with capacitors (no trimming needed)
- Fast ToT using the latch as a local oscillator (up to 800 MHz)

	Inefficiencies (digital) @ 3 GHz/cm <sup>2</sup>
Trigger latency	12.8 µs
Particle loss	<0.1%
Single pixel efficiency	99.9% (digitized 5-bit ToT info except for 0.4% with binary info only)
Ghosts probability	<0.03%

- Temperature range: -40°C/80°C
- Irradiated up to 800 Mrad
- Trimming can correct process and radiation-induced variations with a mismatch < 2%



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